

# Design and simulation implementation of bismuth-doped fiber laser

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**Abstract.** Rare-earth doped fibers are an important means of expanding the wavelength band of optical fibers. Currently, researchers aim to broaden the working wavelength band of optical fibers by doping with different rare-earth elements, thereby increasing the amount of information that can be transmitted. In this paper, a bismuth-doped fiber laser operating around 1300nm was designed. A basic physical model for implementing a bismuth-doped fiber laser was proposed based on the energy levels and transition processes of bismuth, rate, and power propagation equations. It was possible to determine the link between pump power and laser power at a wavelength of 1300 nm by modeling tests using the physical model. Additionally, the relationship between pump light and laser power in bismuth-doped fiber at different positions and propagation directions was analyzed. Suggestions for the future large-scale application of bismuth-doped fiber lasers around the 1300nm wavelength band were provided.

**Keywords:** Bismuth-doped fiber laser, amplified spontaneous emission, power propagation equation

## 1. Introduction

Lasers, with characteristics such as high brightness, monochromaticity, coherence, and good directionality, have been widely used in scientific research, communication, military, industrial, medical, and other fields. With the rapid development of applications such as the internet, 5G, and cloud storage, the global annual information communication volume has surged. Fiber optics communication has become a crucial means of information transmission. Improving information transfer rates is mainly achieved by increasing data transmission and demodulation speeds and expanding the system's transmission bandwidth. Quartz fiber covers the available bandwidth in the range of 1250-1800nm, and by doping fibers with rare earth elements, different spectral bands can be covered to widen the transmission bandwidth [1]. Existing fiber lasers, such erbium-doped fiber amplifiers, only work well in the 1530–1610 nm range, and there are no fiber amplifiers for other wavelengths [2].

The major method used to manufacture erbium-doped fibers is an enhanced chemical vapor deposition procedure in conjunction with solution doping methods [3]. Multiple spatial transmission modes may be supported by these fibers by adjusting parameters including refractive index profile, doping concentration, and core diameter. In 2011, the University of Southampton in the UK first drew a dual-mode erbium-doped fiber, supporting two modes, and achieved gains of over 20 dB in the 1550-1560 nm range using 980 nm laser pumping. Subsequently, various types of dual-mode erbium-doped fibers have emerged, focusing on aspects such as fabrication processes, number of transmission modes,

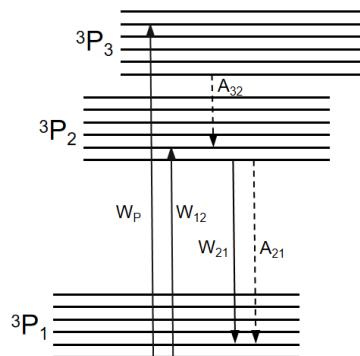
operating wavelengths, gains, differential mode gains, noise, and more [4]. Using dual-mode fibers as transmission lines in space division multiplexing technology requires long-distance transmission, making dual-mode erbium-doped fiber amplifiers crucial devices for compensating for fiber transmission losses [5]. However, in dual-mode erbium-doped fiber amplifiers, high differential mode gain can increase the probability of system interruptions, affecting signal quality [6].

Bismuth, unlike common rare earth elements, has an electron configuration of  $4f^{14}5d^{10}6s^26p^3$ . The inner subshell of bismuth is filled, and the outer 6s and 6p electrons can undergo significant chemical reactions with the host glass components. Therefore, bismuth exhibits emission and absorption characteristics depending on the host material [7]. The oxidation states of multivalent bismuth include  $\text{Bi}^+$ ,  $\text{Bi}^{2+}$ ,  $\text{Bi}^{3+}$ , and  $\text{Bi}^{5+}$ . It is crucial to produce the desired oxidation states in a controlled manner when manufacturing fibers and optical preforms. It is widely believed that when high oxidation states are reduced to low oxidation states, near-infrared fluorescence is produced. However, the preparation process of bismuth-doped fibers depends on various factors such as temperature, pressure, and concentrations of different components, making it challenging to control the oxidation-reduction equilibrium to the appropriate state. Excessive high-valence bismuth ions being reduced and producing bismuth oligomers and metal colloids can lead to a decrease in near-infrared emission centers [8-10]. Regardless of theory and research, there is still controversy over the origin and specific reasons for near-infrared emission centers in bismuth. To boost the efficiency of systems and the performance of bismuth-doped fiber materials, a more thorough investigation into the near-infrared emission characteristics of these fibers is required. Bismuth-doped, Bi/Er co-doped, and quantum dot-doped glasses and fibers can produce ultra-wideband fluorescence covering 1050-1800nm, making them potential gain media for ultra-wideband or even full-band fiber lasers. This widens the utilization of quartz fibers in low-loss communication and expands transmission bandwidth [2,11,12].

In this paper, bismuth-doped fibers are selected as the gain medium. Using a theoretical physics model and numerical simulation methods, a fiber laser working around 1310nm wavelength is designed with laser pumping near 808nm wavelength. This design aims to provide a possibility for the subsequent expansion of fiber working ranges for applications and research in the 1300-1350nm range.

## 2. Theoretical Model

Bi atoms have an outermost electron configuration of  $4f^{14}5d^{10}6s^26p^3$ . The ground state energy level of Bi ions is  $3P_0$ , therefore, absorption spectral lines occur at  $0.5\mu\text{m}$ ,  $0.7\mu\text{m}$ ,  $0.8\mu\text{m}$ , and  $1.0\mu\text{m}$  when electrons transition from  $3P^0$  to  $1S^0$ ,  $3P^0$  to  $1D^2$ ,  $3P^0$  to  $1P^2$ , and  $3P^0$  to  $1P^1$ , respectively [13]. Thus, a three-level system is used to describe the transition process as shown in Figure 1. Utilizing an 808nm pump light source, electrons are excited to the  $3P^2$  level. Particles on the  $3P^0$  level undergo spontaneous emission transition to the  $3P^1$  level, while some particles on the  $3P^2$  level undergo non-radiative transition to the  $3P^1$  level. Particles on the  $3P^1$  level then undergo stimulated emission and non-radiative transitions back to the first level [14].  $W_p$  represents the pump light absorption rate,  $W_{12}$  is the signal light absorption rate,  $W_{21}$  is the stimulated emission rate of the signal light,  $A_{32}$  is the non-radiative transition rate, and  $A_{21}$  is the radiative transition rate.



**Figure 1.** Schematic diagram of the transition between three energy levels of Bi

In Fig. 1, The transition rate equations for the electron between the three energy levels can be obtained as follows:

$$\frac{\partial N_1(z)}{\partial t} = -[W_p(z) + W_{12}(z)]N_1(z) + A_{21}N_2(z) + W_{21}(z)N_2(z) \quad (1)$$

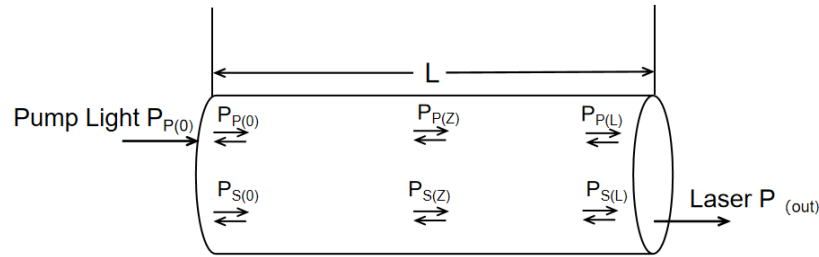
$$\frac{\partial N_2(z)}{\partial t} = W_{12}(z)N_1(z) - W_{21}(z)N_2(z) - A_{21}N_2(z) + A_{32}N_3(z) \quad (2)$$

$$\frac{\partial N_3(z)}{\partial t} = W_p(z)N_1(z) - A_{32}N_3(z) \quad (3)$$

$$N = N_1(z) + N_2(z) + N_3(z) \quad (4)$$

Where  $W_p(z) = \frac{\sigma_{13}P_p(z)}{\ln_{13} A_{eff}}$ ,  $W_{12}(z) = \frac{\sigma_{12}(v_{12})(z)}{\ln_{12} A_{eff}}$ ,  $W_{21}(z) = \frac{\sigma_{21}(v_{21})(z)}{\ln_{21} A_{eff}}$ ,  $A_{eff} = \pi r^2$ .

Where the following are represented in units of per second (/s):  $W_p(z)$ ,  $W_{12}(z)$ ,  $W_{21}(z)$ ,  $A_{32}(z)$ ,  $A_{21}(z)$  denote the pump light absorption rate, signal light absorption rate, stimulated emission rate of signal light, non-radiative transition rate, and radiative transition rate, respectively.  $r$  is the radius of the optical fiber core.  $P_p$  and  $P_s$  denote the pump power and stimulated emission power, respectively. The cross-sections for pump light absorption, signal light absorption, and signal light emission are  $\sigma_{13}$ ,  $\sigma_{12}$ , and  $\sigma_{21}$  respectively. The optical fiber's cross-sectional area is denoted by  $A_{eff}$ . Fig. 2 depicts the propagation of laser and pump light power in the optical fiber.



**Figure 2.** Diagrammatic representation of how laser and pump light powers propagate across optical fibers

From Fig. 2, the propagation equations for laser power and pump light in bismuth-doped optical fiber may be obtained as follows.

$$\frac{dP_p^+(z)}{dz} = \Gamma_p(-\sigma_{13}N_1(z) - \alpha_p)(z) \quad (5)$$

$$\frac{dP_p^-(z)}{dz} = -\Gamma_p(-\sigma_{13}N_1(z) - \alpha_p)(z) \quad (6)$$

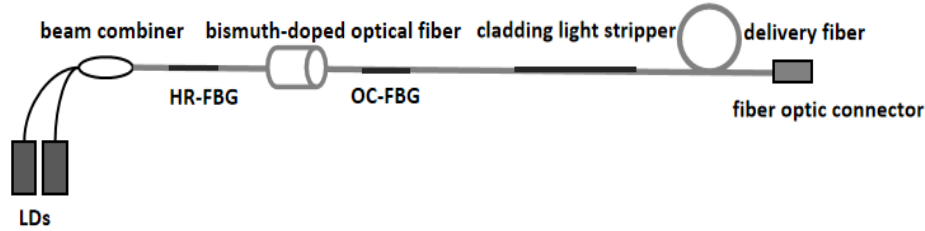
$$\frac{dP_s^+(z)}{dz} = \Gamma_s[\sigma_{21}N_2(z) - \sigma_{12}N_1(z) - \alpha_s](z) \quad (7)$$

$$\frac{dP_s^-(z)}{dz} = -\Gamma_s[\sigma_{21}N_2(z) - \sigma_{12}N_1(z) - \alpha_s](z) \quad (8)$$

### 3. Design and Simulation Experiment of Laser

Design a single-end pump-pumped bismuth-doped fiber laser for the simulation experiment model. LDs are fiber-coupled semiconductor lasers providing pump light to the laser. Lower-power pump light is combined with higher-power pump light using a beam combiner and injected into the bismuth-doped fiber. The fiber doped with bismuth exhibits a high reflectivity. Bragg grating and a fiber with low reflectance Pump light and laser are able to oscillate back and forth in the fiber due to the bragg grating on both ends. The laser emitted from the bismuth-doped fiber passes through a cladding light stripper

and is then transmitted through a delivery fiber to the fiber optic connector. Finally, it is collimated and output from the fiber optic connector.



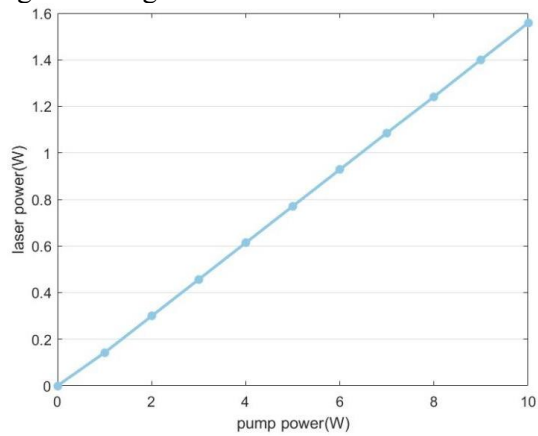
**Figure 3.** Design structure diagram of bismuth-doped fiber laser

Here is the simulated experimental data based on [13,14], presented in the following Table 1.

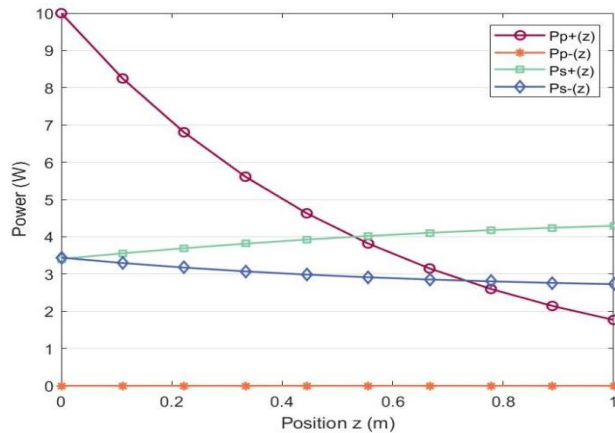
**Table 1.** Experimental parameters in the rate equation and power propagation equation

Symbol	Physical Parameter	Numerical Value	Unit
$\lambda_{sp}$	Pump light central wavelength	$8.08 \cdot 10^{-7}$	m
$\lambda_s$	Fiber laser central wavelength	$1.3 \cdot 10^{-6}$	m
$\tau$	Bismuth ion average level lifetime	$5 \cdot 10^{-4}$	s
$\sigma_{13}$	Pump light absorption cross-section	$1.3 \cdot 10^{-28}$	$m^2$
$\sigma_{31}$	Pump light emission cross-section	$2 \cdot 10^{-29}$	$m^2$
$\sigma_{12}$	Stimulated emission absorption cross-section	$1 \cdot 10^{-28}$	$m^2$
$\sigma_{21}$	Stimulated emission emission cross-section	$1 \cdot 10^{-28}$	$m^2$
$A_{eff}$	Core cross-sectional area	$2 \cdot 10^{-11}$	$m^2$
$N$	Number of bismuth ions in the core	$1.8 \cdot 10^{24}$	count
$\alpha_p$	Dual-clad fiber loss for pump light	$2 \cdot 10^{-3}$	$m^{-1}$
$\alpha_s$	Dual-clad fiber loss for laser light	$4 \cdot 10^{-4}$	$m^{-1}$
$L$	Dual-clad fiber length	1	m
$\Gamma_p$	Pump light power fill factor	0.82	/
$\Gamma_s$	Laser power fill factor	0.74	/
$R_1$	Left boundary mirror reflectivity	0.99	/
$R_2$	Right boundary mirror reflectivity	0.635	/

By substituting the above parameters into the model and performing numerical simulations in Matlab, Fig. 4 and Fig. 5 are obtained.



**Figure 4.** The connection between pump power and laser power



**Figure 5.** Pump power and laser power relationship as a function of location

Based on the analysis of Fig. 4 by taking data points, we find that the laser power increases nonlinearly with increasing pump power. At a pump power of 3W, the laser power is found to be 0.4563W. Additionally, from Fig. 5, it is possible to acquire the strength of the laser and pump light at various points along the forward and reverse propagation paths. It can also be observed from the figure that when the pump light propagates forward to the right boundary, there is still a power of approximately 1.9W, which means that increasing the length of the laser can lead to greater laser power.

#### 4. Conclusion

In conclusion, this paper presents the energy levels and structure of electron transitions in bismuth-doped fiber, the physical model, and simulation results. From the simulation results, it is evident that within a certain range, the larger the pump power of the bismuth-doped fiber laser, the greater the output laser power. Additionally, in this simulation experiment, a bismuth-doped fiber length of 1m was used. However, it was found at the right boundary that nearly 1/5 of the pump power was not consumed. This suggests that increasing the fiber length could enhance the consumption rate of pump power. It is crucial to identify a relatively short fiber length where the majority of the pump power is used in order to increase the laser system's efficiency and save expenses. This lays the foundation for future large-scale applications of bismuth-doped fiber in the vicinity of the 1300nm wavelength band. Bismuth-doped fiber is also becoming an important material for expanding the range of fiber wavelengths, even forming a laser gain medium for the entire wavelength range. The bismuth-doped laser created in this study operates in the 1300 nm wavelength range. Based on the properties of bismuth-doped fiber, lasers for additional wavelength bands may be built in the future.

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